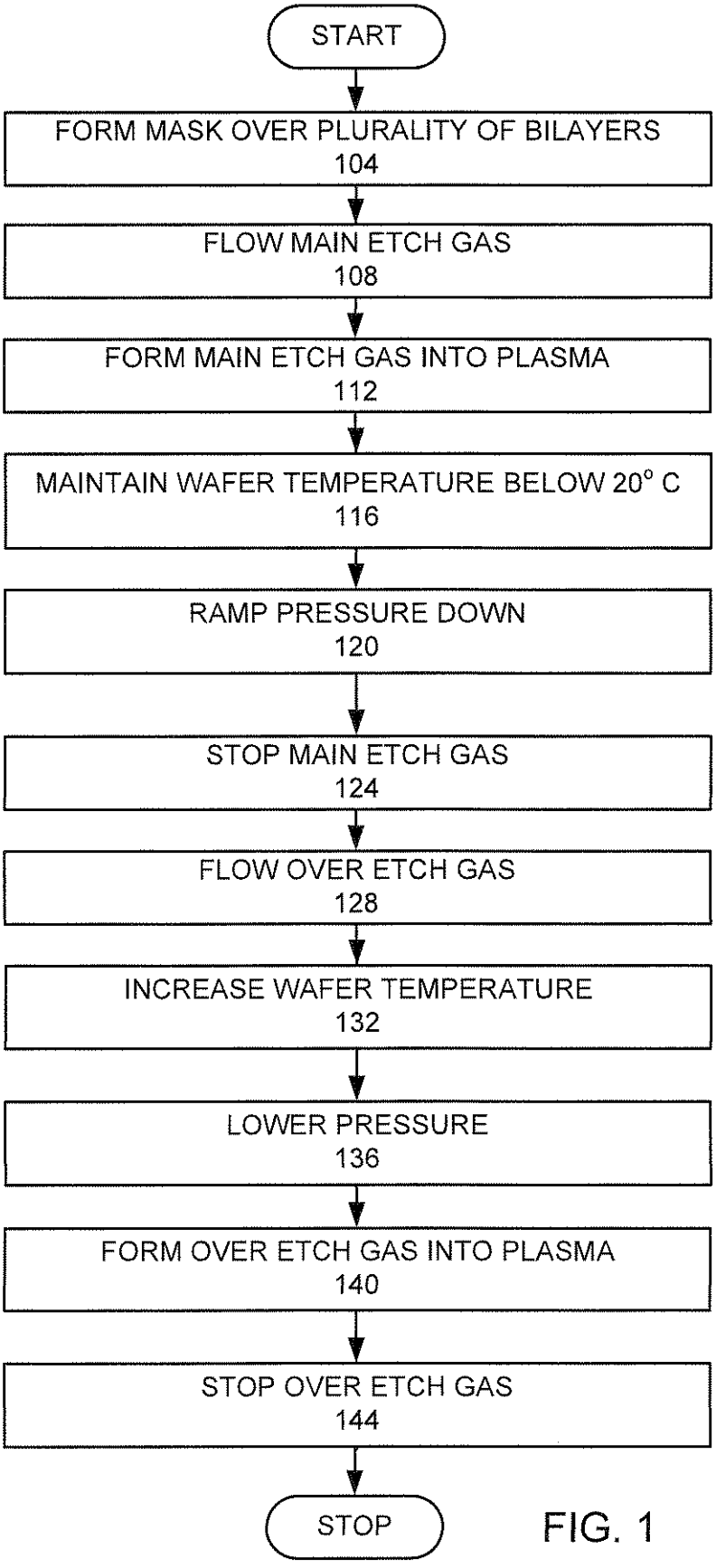

START
FORM MASK OVER PLURALITY OF BILAYERS
104
FLOW MAIN ETCH GAS
108
FORM MAIN ETCH GAS INTO PLASMA
112
MAINTAIN WAFER TEMPERATURE BELOW 20° C
116
RAMP PRESSURE DOWN
120
STOP MAIN ETCH GAS
124
FLOW OVER ETCH GAS
128
INCREASE WAFER TEMPERATURE
132
LOWER PRESSURE
136
FORM OVER ETCH GAS INTO PLASMA
140
STOP OVER ETCH GAS
144
STOP

FIG. 1

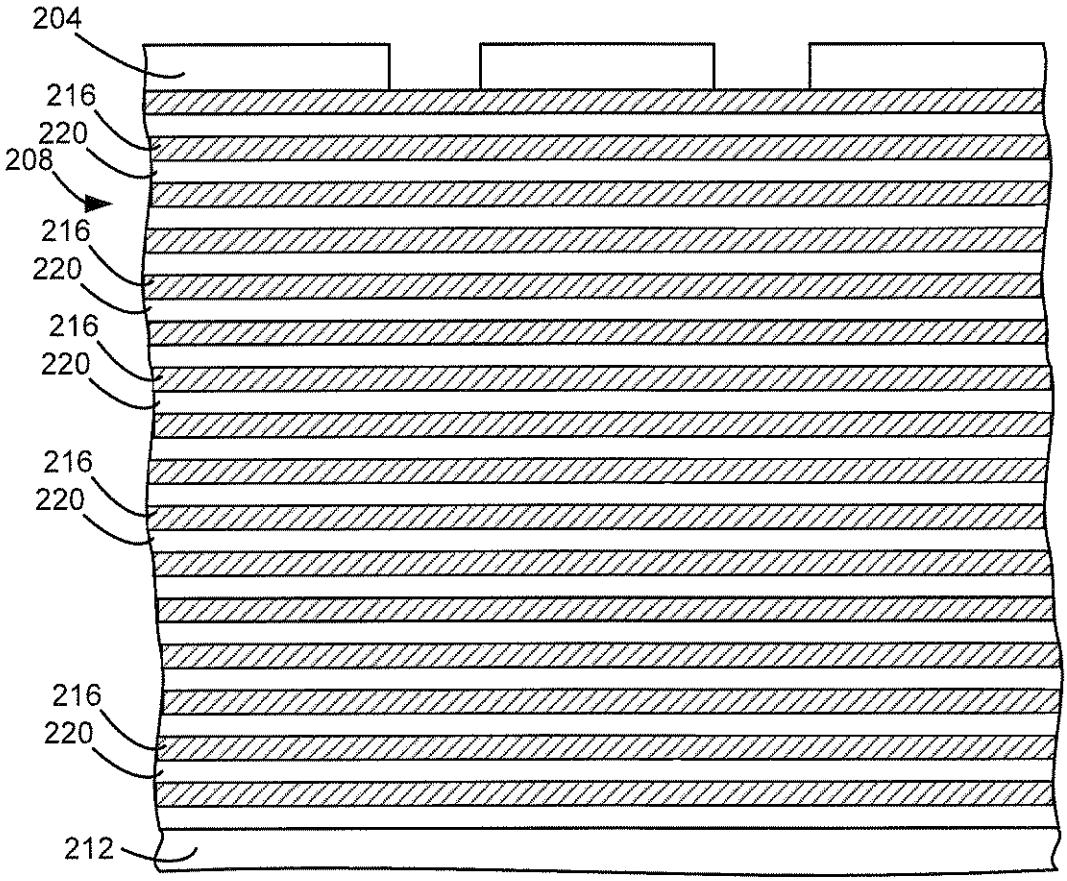


FIG. 2A

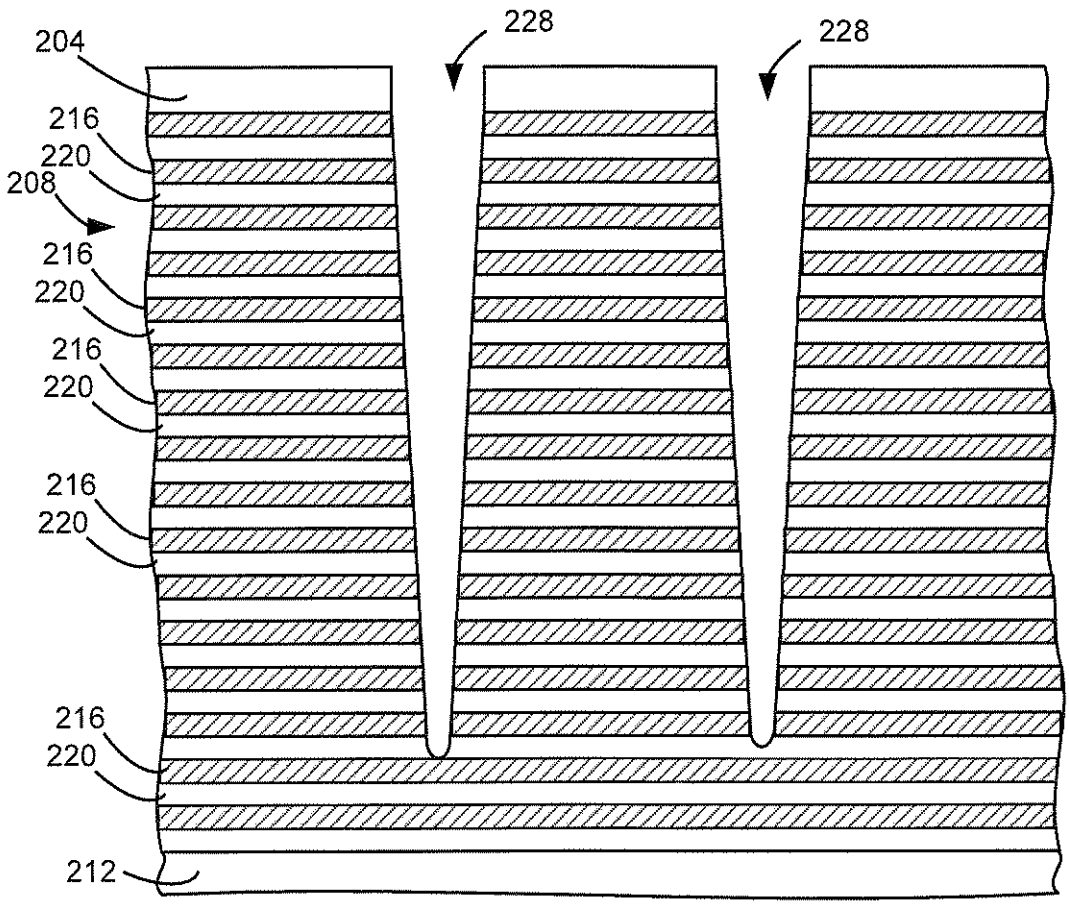


FIG. 2B

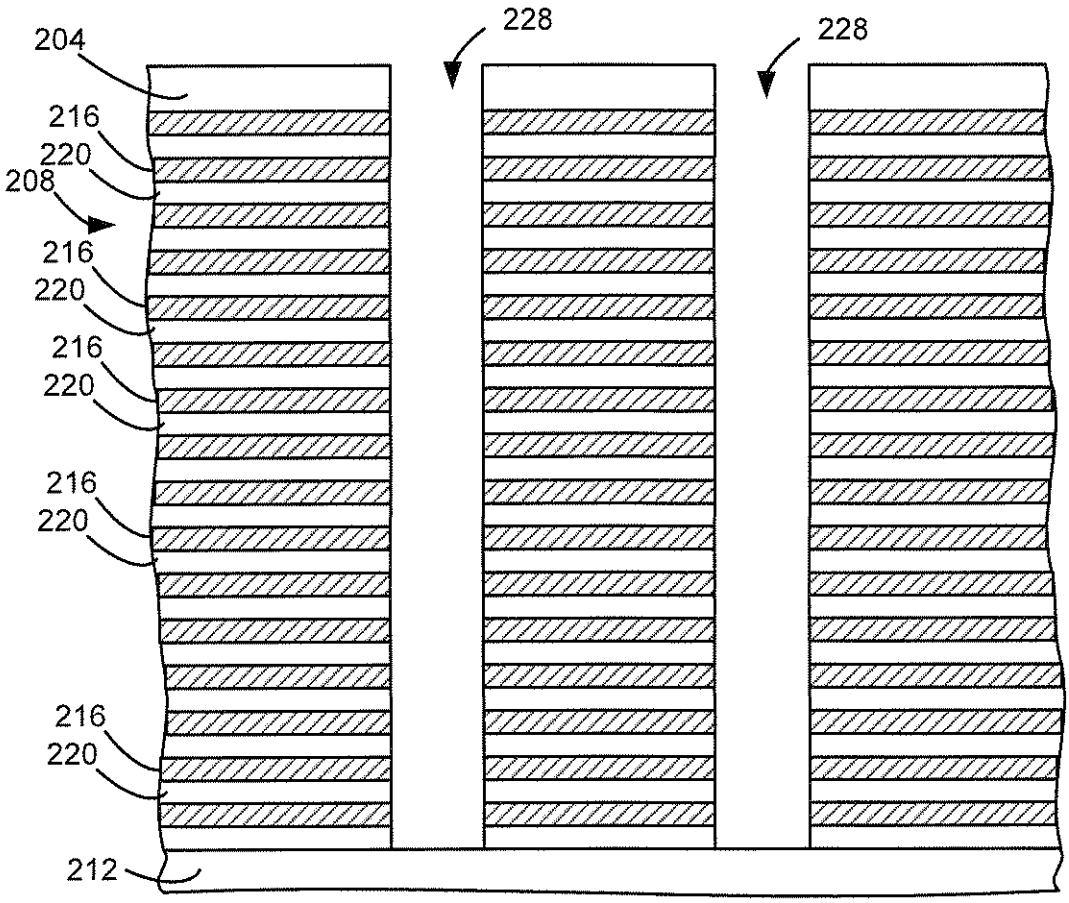


FIG. 2C

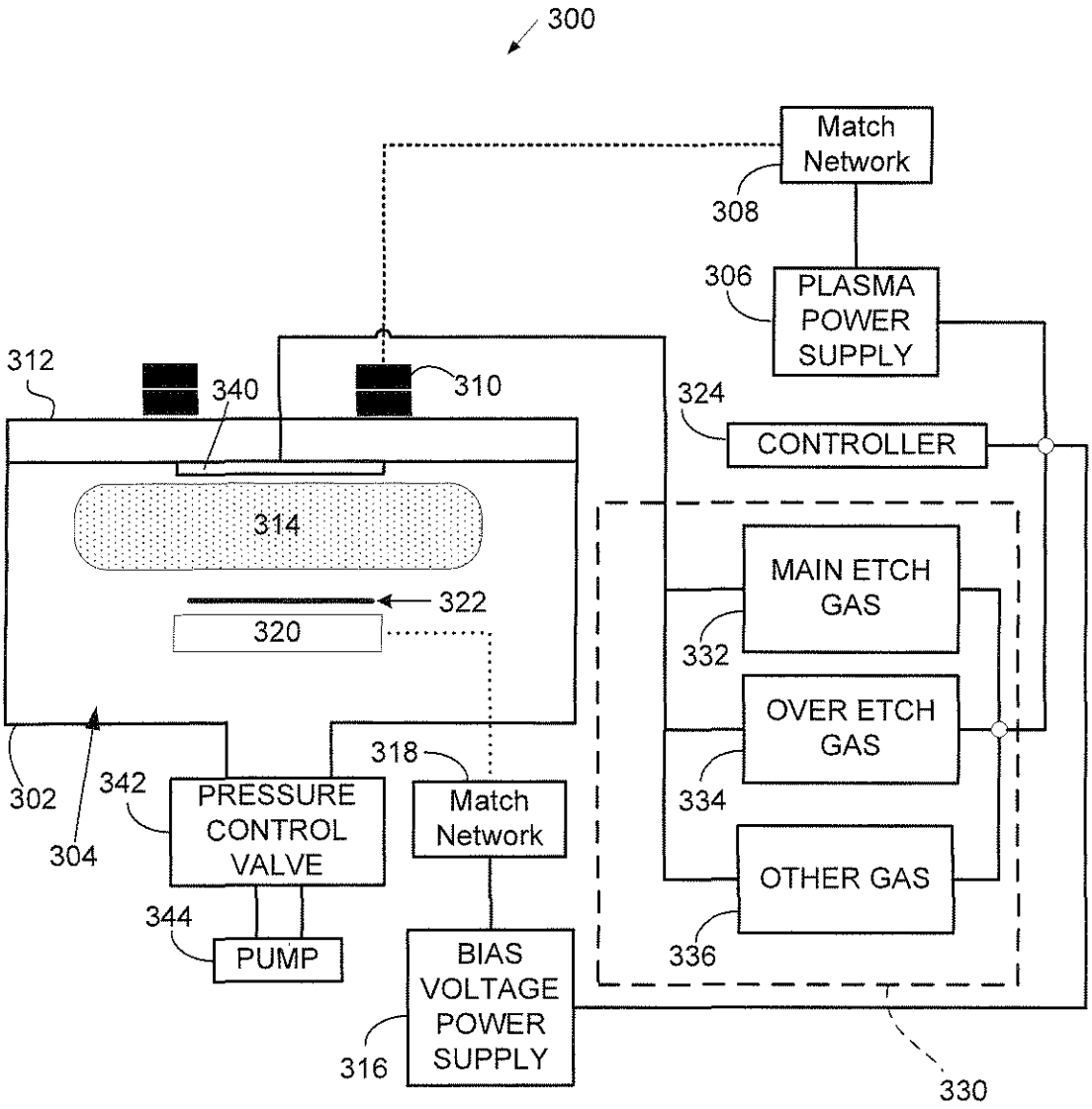

300
Match Network
308
306
PLASMA POWER SUPPLY
312
340
310
324
CONTROLLER
314
322
320
MAIN ETCH GAS
332
OVER ETCH GAS
334
OTHER GAS
336
318
302
342
304
PRESSURE CONTROL VALVE
Match Network
344
PUMP
BIAS VOLTAGE POWER SUPPLY
316
330

FIG. 3

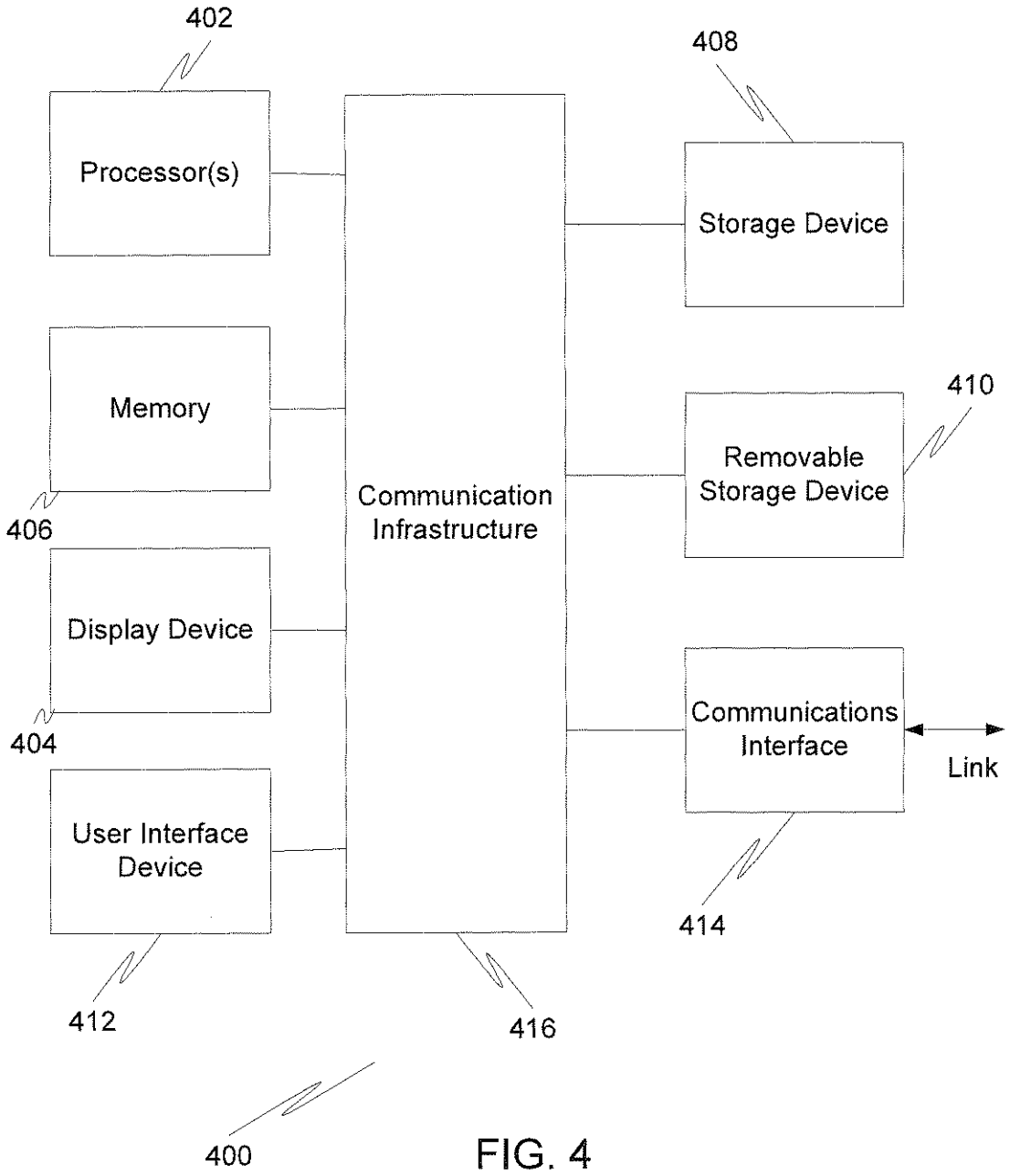

402
Processor(s)
408
Storage Device
Memory
406
Communication Infrastructure
410
Removable Storage Device
Display Device
404
Communications Interface
Link
User Interface Device
414
412
416
400

FIG. 4

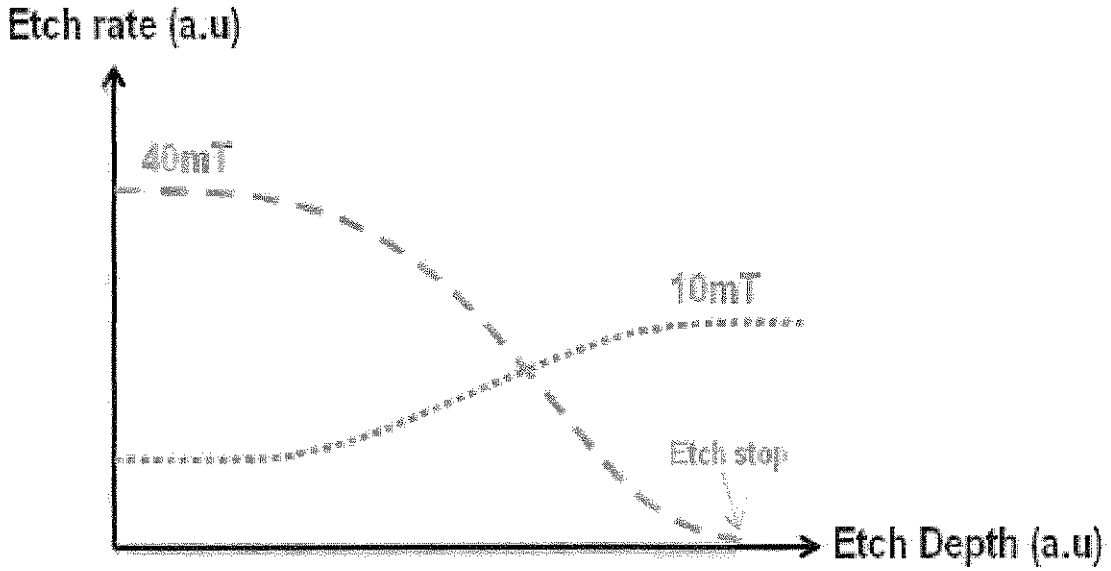


FIG. 5